

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF THE CLAIMS:

Claims 1-4 (Cancelled).

5. (Currently Amended) ~~The~~ A semiconductor memory element ~~of claim 1,~~ comprising:

a well region having a first conductivity type and formed in a principal surface of a semiconductor substrate;

source and drain regions each having a second conductivity type and formed in said well region to have a specified distance therebetween;

first and second gates and first and second charge storage regions formed, via a first insulating film, on a portion of the principal surface of said semiconductor substrate between said source and drain regions; and

a third gate formed over said first and second charge storage regions via a second insulating film, said first and second charge storage regions being provided between said first and second gates,

wherein each of said first and second charge storage regions has a layer composed of stacked a plurality of semiconductor nano-crystals.

Claims 6-7 (Cancelled)

8. (Currently Amended) ~~The~~ A semiconductor memory element of claim 1, comprising:

a well region having a first conductivity type and formed in a principal surface of a semiconductor substrate;  
source and drain regions each having a second conductivity type and formed in said well region to have a specified distance therebetween;

first and second gates and first and second charge storage regions formed, via a first insulating film, on a portion of the principal surface of said semiconductor substrate between said source and drain regions; and

a third gate formed over said first and second a charge storage regions via a second insulating film, said first and second charge storage regions being provided between said first and second gates,

wherein each of said first and second charge storage regions has a respective floating gate composed of polysilicon.

Claims 9-30 (Cancelled)

31. (New) The semiconductor memory element of claim 5, wherein said nano-crystals are silicon nano-crystals.

32. (New) The semiconductor memory element of claim 31, wherein said nano-crystals are insulated from each other.

33. (New) The semiconductor memory element of claim 32, wherein said nano-crystals are oxidized.

34. (New) The semiconductor memory element of claim 32, wherein said nano-crystals are nitrided.

35. (New) The semiconductor memory element of claim 5, wherein said nano-crystals are insulated from each other.

36. (New) The semiconductor memory element of claim 35, wherein said nano-crystals are oxidized.

37. (New) The semiconductor memory element of claim 35, wherein said nano-crystals are nitrided.